

Anna Marzegalli

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

30
papers

403
citations

9
h-index

19
g-index

33
ext. papers

500
ext. citations

6.2
avg, IF

3.16
L-index

#	Paper	IF	Citations
30	Scaling hetero-epitaxy from layers to three-dimensional crystals. <i>Science</i> , 2012 , 335, 1330-4	33.3	125
29	Unexpected dominance of vertical dislocations in high-misfit ge/si(001) films and their elimination by deep substrate patterning. <i>Advanced Materials</i> , 2013 , 25, 4408-12	24	47
28	Perfect crystals grown from imperfect interfaces. <i>Scientific Reports</i> , 2013 , 3, 2276	4.9	28
27	Photodetection in Hybrid Single-Layer Graphene/Fully Coherent Germanium Island Nanostructures Selectively Grown on Silicon Nanotip Patterns. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 2017-26	9.5	25
26	In-plane selective area InSb/Al nanowire quantum networks. <i>Communications Physics</i> , 2020 , 3,	5.4	18
25	Temperature-Dependent Stability of Polytypes and Stacking Faults in SiC: Reconciling Theory and Experiments. <i>Physical Review Applied</i> , 2019 , 12,	4.3	17
24	3D heteroepitaxy of mismatched semiconductors on silicon. <i>Thin Solid Films</i> , 2014 , 557, 42-49	2.2	16
23	Onset of vertical threading dislocations in Si _{1-x} Ge _x /Si (001) at a critical Ge concentration. <i>APL Materials</i> , 2013 , 1, 052109	5.7	13
22	Extended defects in 3C-SiC: Stacking faults, threading partial dislocations, and inverted domain boundaries. <i>Acta Materialia</i> , 2021 , 213, 116915	8.4	11
21	Exceptional thermal strain reduction by a tilting pillar architecture: Suspended Ge layers on Si (001). <i>Materials and Design</i> , 2017 , 116, 144-151	8.1	9
20	The origin and nature of killer defects in 3C-SiC for power electronic applications by a multiscale atomistic approach. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 8380-8392	7.1	9
19	3C-SiC Epitaxy on Deeply Patterned Si(111) Substrates. <i>Materials Science Forum</i> , 2016 , 858, 151-154	0.4	9
18	Molecular dynamics simulations of extended defects and their evolution in 3CSiC by different potentials. <i>Modelling and Simulation in Materials Science and Engineering</i> , 2020 , 28, 015002	2	8
17	Lattice tilt and strain mapped by X-ray scanning nanodiffraction in compositionally graded SiGe/Si microcrystals. <i>Journal of Applied Crystallography</i> , 2018 , 51, 368-385	3.8	8
16	Strain Engineering in Highly Mismatched SiGe/Si Heterostructures. <i>Materials Science in Semiconductor Processing</i> , 2017 , 70, 117-122	4.3	7
15	Structure and Stability of Partial Dislocation Complexes in 3C-SiC by Molecular Dynamics Simulations. <i>Materials</i> , 2019 , 12,	3.5	6
14	Dynamics of crosshatch patterns in heteroepitaxy. <i>Physical Review B</i> , 2019 , 100,	3.3	6

13	Misfit-Dislocation Distributions in Heteroepitaxy: From Mesoscale Measurements to Individual Defects and Back. <i>Physical Review Applied</i> , 2018 , 10,	4.3	6
12	New Approaches and Understandings in the Growth of Cubic Silicon Carbide. <i>Materials</i> , 2021 , 14,	3.5	6
11	Burgers Vector Analysis of Vertical Dislocations in Ge Crystals by Large-Angle Convergent Beam Electron Diffraction. <i>Microscopy and Microanalysis</i> , 2015 , 21, 637-45	0.5	5
10	Lattice bending in three-dimensional Ge microcrystals studied by X-ray nanodiffraction and modelling. <i>Journal of Applied Crystallography</i> , 2016 , 49, 976-986	3.8	5
9	Solving the critical thermal bowing in 3C-SiC/Si(111) by a tilting Si pillar architecture. <i>Journal of Applied Physics</i> , 2018 , 123, 185703	2.5	5
8	Structure, interface abruptness and strain relaxation in self-assisted grown InAs/GaAs nanowires. <i>Applied Surface Science</i> , 2017 , 395, 29-36	6.7	4
7	Mechanism of stacking fault annihilation in 3C-SiC epitaxially grown on Si(001) by molecular dynamics simulations. <i>CrystEngComm</i> , 2021 , 23, 1566-1571	3.3	3
6	Unexpected Dominance of Vertical Dislocations in High-Misfit Ge/Si(001) Films and Their Elimination by Deep Substrate Patterning (Adv. Mater. 32/2013). <i>Advanced Materials</i> , 2013 , 25, 4407-4407 ²⁴		2
5	Strained MOSFETs on ordered SiGe dots. <i>Solid-State Electronics</i> , 2011 , 65-66, 81-87	1.7	2
4	Atomic-scale insights on the formation of ordered arrays of edge dislocations in Ge/Si(001) films via molecular dynamics simulations.. <i>Scientific Reports</i> , 2022 , 12, 3235	4.9	2
3	Strained MOSFETs on ordered SiGe dots 2010 ,		1
2	Nature and Shape of Stacking Faults in 3C-SiC by Molecular Dynamics Simulations. <i>Physica Status Solidi (B): Basic Research</i> , 2021 , 258, 2000598	1.3	0
1	Stress engineering of boron doped diamond thin films via micro-fabrication. <i>APL Materials</i> , 2021 , 9, 061109	1.9	0